

IN THE CLAIMS:

Claim 1 (original) A process for producing a semiconductor device comprising:
a step of forming a gate electrode on a semiconductor substrate by performing a lithographic step using a reticle pattern provided with a substantially linear gate electrode pattern which comprises at least two transistor regions and contact regions formed between these transistors and has paired first and second long sides and a pair of short sides, wherein a projecting portion in which at least a part of the contact region is arranged is included in the first long side and a concave portion facing at least the entire length of the projecting portion is included in the second long side facing the first long side between the transistor regions of the reticle pattern.

Claims 2-13 (Cancelled)